

TOSHIBA TRANSISTOR SILICON PNP EPITAXIAL TYPE (PCT PROCESS)

2SB905

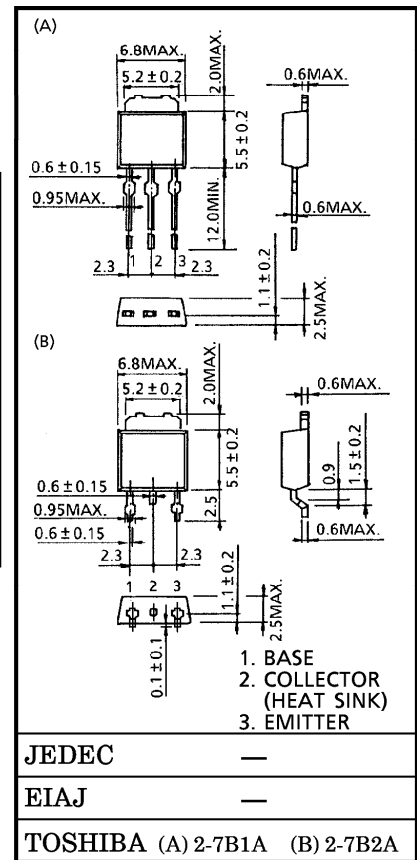
POWER AMPLIFIER APPLICATIONS

Unit in mm

- Complementary to 2SD1220

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V _{CB0}	-150	V
Collector-Emitter Voltage	V _{CEO}	-150	V
Emitter-Base Voltage	V _{EBO}	-6	V
Collector Current	I _C	-1.5	A
Base Current	I _B	-1.0	A
Collector Power Dissipation	P _C	1.0	W
		T _a = 25°C	
		10	
		T _c = 25°C	
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	-55~150	°C



ELECTRICAL CHARACTERISTICS (Ta = 25°C)

Weight : 0.36 g

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I _{CBO}	V _{CB} = -150 V, I _E = 0	—	—	-1.0	μA
Emitter Cut-off Current	I _{EBO}	V _{EB} = -6 V, I _C = 0	—	—	-1.0	μA
Collector-Emitter Breakdown Voltage	V (BR) CEO	I _C = -10 mA, I _B = 0	-150	—	—	V
DC Current Gain	h _{FE} (Note)	V _{CE} = -5 V, I _C = -200 mA	60	—	320	
Collector-Emitter Saturation Voltage	V _{CE} (sat)	I _C = -500 mA, I _B = -50 mA	—	—	-1.5	V
Base-Emitter Voltage	V _{BE}	V _{CE} = -5 V, I _C = -5 mA	-0.5	—	-0.8	V
Transition Frequency	f _T	V _{CE} = -5 V, I _C = -200 mA	15	50	—	MHz
Collector Output Capacitance	C _{ob}	V _{CB} = -10 V, I _E = 0, f = 1 MHz	—	—	35	pF

Note : h_{FE} Classification R : 60~120, O : 100~200, Y : 160~320

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